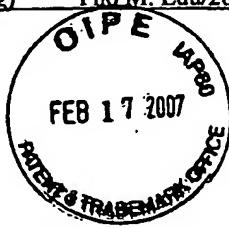


2-20-07

IFW



Appn. Number: 10/609.157

Appn. Filed: Jun/27/2003

Applicant: Hai Jiang

Title: Programmable Metallization Cell Memory with  
Multiple Extra-Small Resistive Elements

Examiner: Pho M. Luu/2824

Please do not  
enter  
3/20/07  
VTN

Feb. 15, 2007

Pleasanton, CA

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir,

Below are the response to the Office Action mailed on Nov. 28, 2006 and new  
claim status:

**Claim rejections-35USC 102**

*Claim 32-34 are rejected under 35 U.S.C. 102(e) as being anticipated by  
Gliton. (US.2003/0194865).*

*Regarding claims 32-34, Gliton in Figure 3 disclosed a memory device  
(memory cell 120) comprising:*

*A resistive layer with a plurality of solid electrolyte element (110) and a  
metallic layer(112) and wherein the resistive layer is a layer with plurality of solid  
electrolyte element(110)embedded in an insulator layer(200) and wherein the*